

NTHS4501N

Power MOSFET

30 V, 6.7 A, Single N-Channel, ChipFET™ Package

Features

- Planar Technology Device Offers Low $R_{DS(on)}$ and Fast Switching Speed in a ChipFET Package
- Leadless ChipFET Package has 40% Smaller Footprint than TSOP-6. Ideal Device for Applications Where Board Space is at a Premium.
- ChipFET Package Exhibits Excellent Thermal Capabilities Where Heat Transfer is Required.
- Pb-Free Package is Available

Applications

- Buck and Boost Converters
- Optimized for Battery and Load Management Applications in Portable Equipment such as Notebook Computers, MP3 Players, Cell Phones, Digital Cameras, Personal Digital Assistants and Other Portable Applications
- Charge Control in Battery Chargers

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	30	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$	A
			$T_A = 85^\circ\text{C}$	
	$t \leq 5 \text{ s}$		$T_A = 25^\circ\text{C}$	
Power Dissipation (Note 1)	Steady State	P_D	$T_A = 25^\circ\text{C}$	W
			$T_A = 85^\circ\text{C}$	
	$t \leq 5 \text{ s}$		$T_A = 25^\circ\text{C}$	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	20	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	1.1	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	95	$^\circ\text{C/W}$
Junction-to-Foot (Drain) Steady State (Note 1)	$R_{\theta JF}$	20	
Junction-to-Ambient – $t \leq 5 \text{ s}$ (Note 1)	$R_{\theta JA}$	50	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

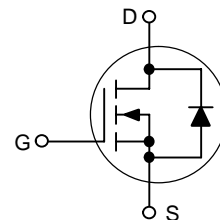
- Surface Mounted on FR4 Board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).



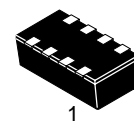
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DS}$	$R_{DS(on)}$ Typ	I_D Max
30 V	30 m Ω @ 10 V	6.7 A
	40 m Ω @ 4.5 V	

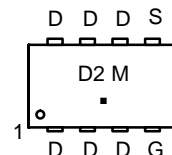


N-Channel MOSFET



ChipFET
CASE 1206A
STYLE 1

MARKING DIAGRAM AND PIN ASSIGNMENT



D2 = Specific Device Code
M = Month Code
■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTHS4501NT1	ChipFET	3000/Tape & Reel
NTHS4501NT1G	ChipFET (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTHS4501N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30	31		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			30		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.0	1.6	2.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.0		mV/ $^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.9\text{ A}$		30	38	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.9\text{ A}$		40	50	
Forward Transconductance	g_{FS}	$V_{DS} = 10\text{ V}, I_D = 4.9\text{ A}$		15		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 24\text{ V}$		462		pF
Output Capacitance	C_{OSS}			137		
Reverse Transfer Capacitance	C_{RSS}			32		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 4.9\text{ A}$		9.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.7		
Gate-to-Source Charge	Q_{GS}			1.3		
Gate-to-Drain Charge	Q_{GD}			1.8		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 1.0\text{ A}, R_G = 6.0\text{ }\Omega$		4.0		ns
Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			17		
Fall Time	t_f			7.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 1.1\text{ A}$	$T_J = 25^\circ\text{C}$		0.75	1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 1.1\text{ A}, dI_S/dt = 90\text{ A}/\mu\text{s}$			19.1		ns
Charge Time	t_a				11.9		
Discharge Time	t_b				7.3		
Reverse Recovery Charge	Q_{RR}				13		nC

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

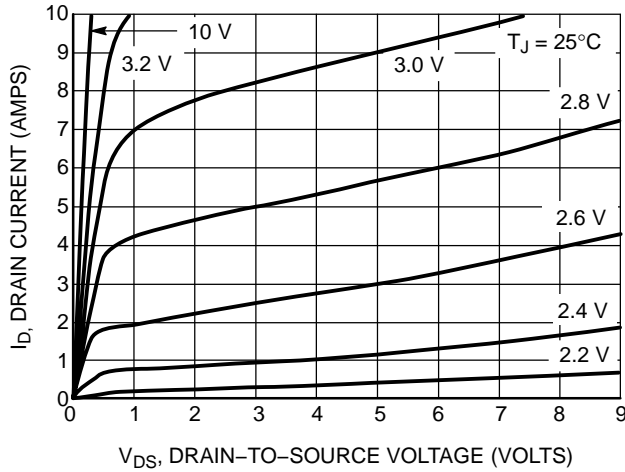


Figure 1. On-Region Characteristics

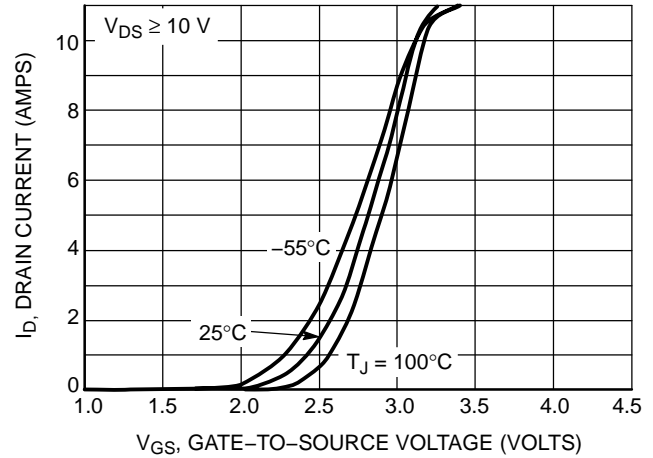


Figure 2. Transfer Characteristics

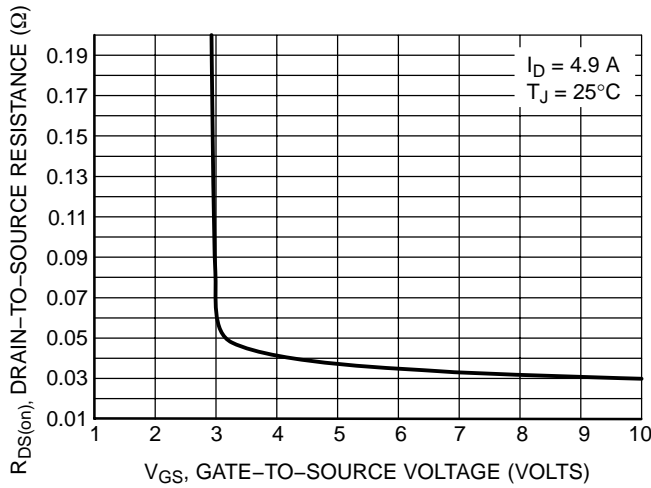


Figure 3. On-Resistance vs. Gate-to-Source Voltage

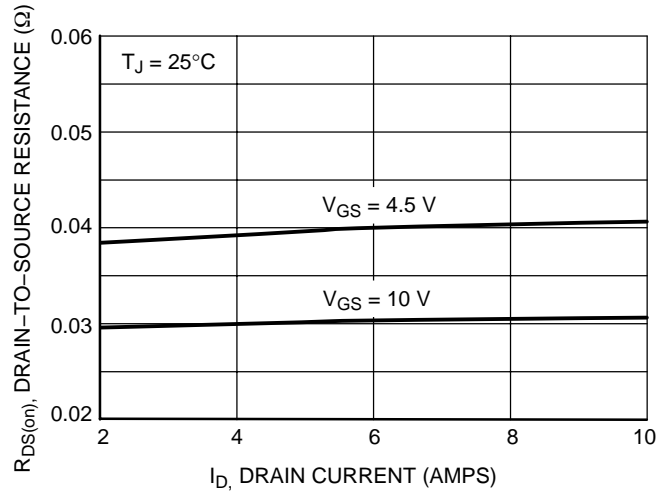


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

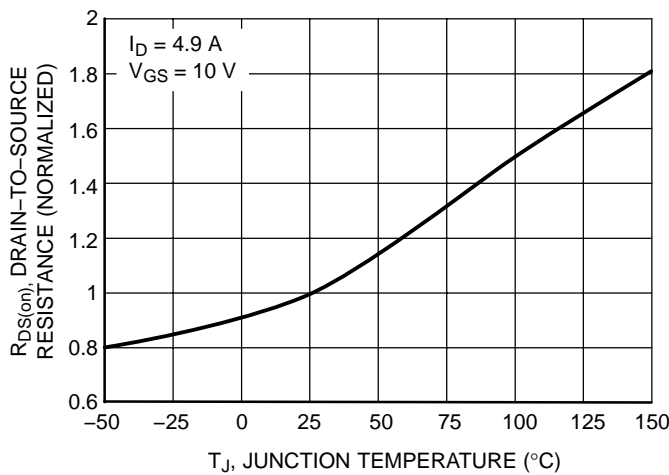


Figure 5. On-Resistance Variation with Temperature

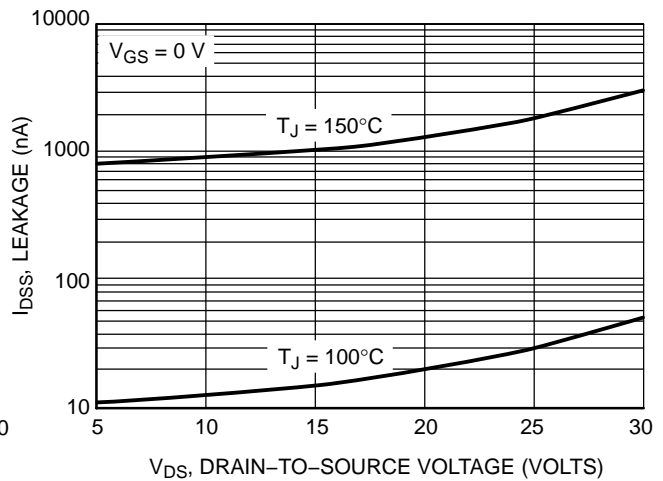


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

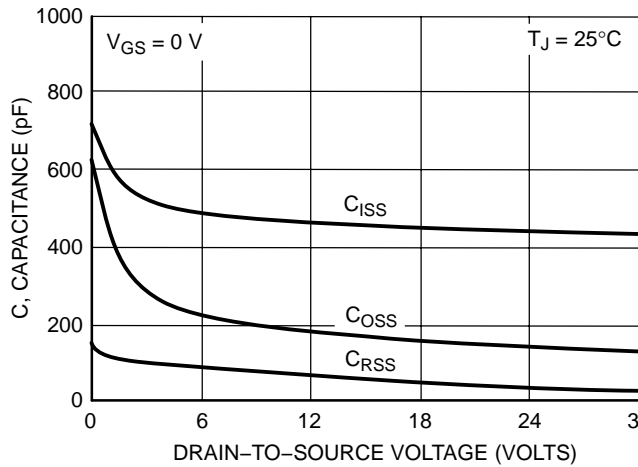


Figure 7. Capacitance Variation

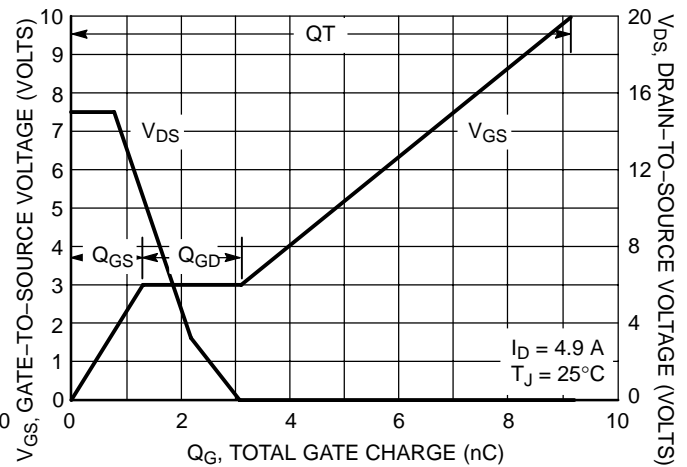


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

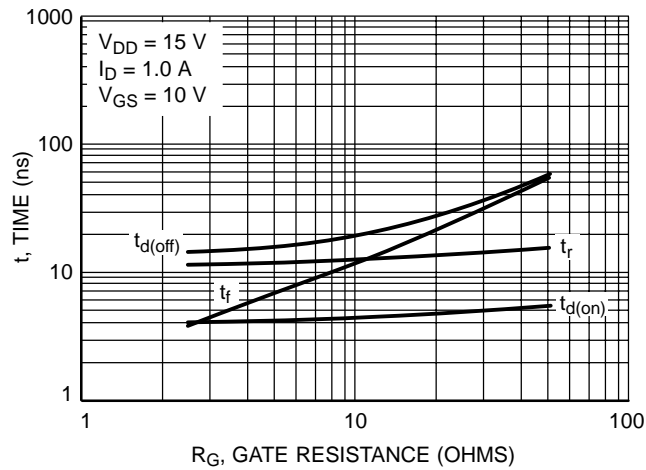


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

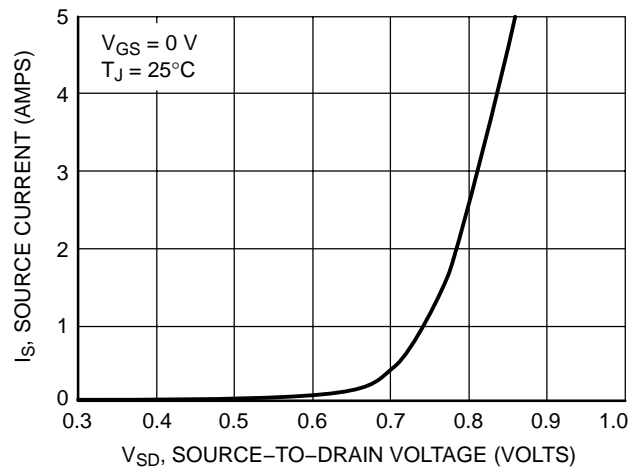
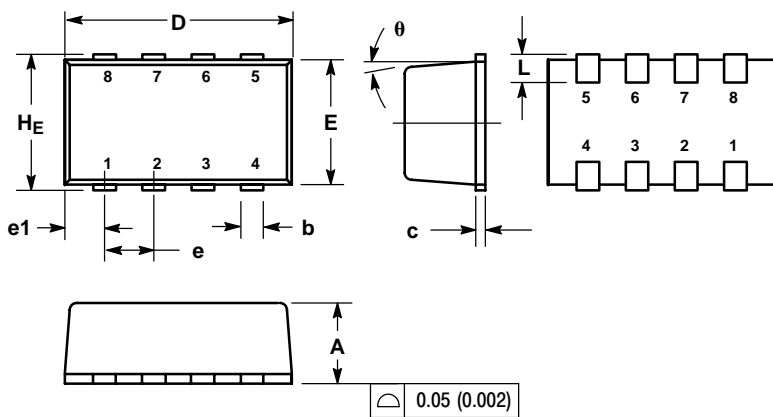


Figure 10. Diode Forward Voltage vs. Current

NTHS4501N

PACKAGE DIMENSIONS

ChipFET™
CASE 1206A-03
ISSUE H



NOTES:

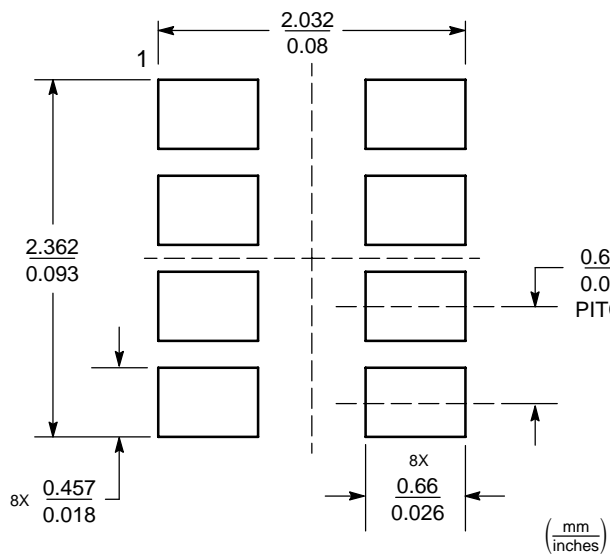
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
HE	1.80	1.90	2.00	0.071	0.075	0.079
theta	5° NOM			5° NOM		

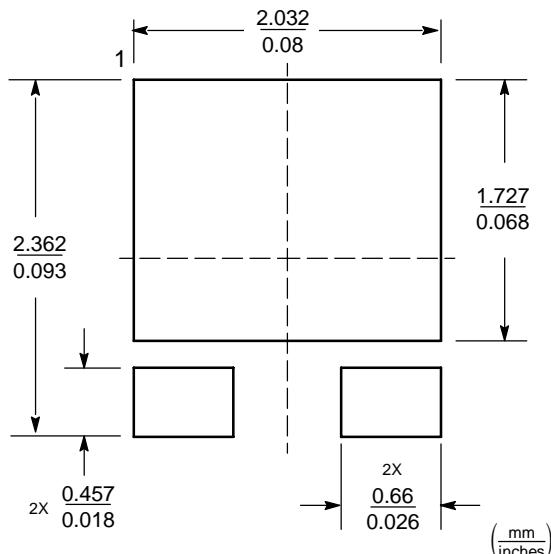
STYLE 1:

- PIN 1. DRAIN
- DRAIN
- DRAIN
- GATE
- SOURCE
- DRAIN
- DRAIN
- DRAIN

SOLDERING FOOTPRINTS*




Basic



Style 1

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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